Ignasi Fina

List of Publications by Year in descending order

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143 papers	8,046 citations	66343 42 h-index	51608 86 g-index
148 all docs	148 docs citations	148 times ranked	7896 citing authors

#	Article	IF	Citations
1	Positive Effect of Parasitic Monoclinic Phase of Hf_{0.5}Zr_{0.5}O₂ on Ferroelectric Endurance. Advanced Electronic Materials, 2022, 8, 2100420.	5.1	14
2	Improved polarization and endurance in ferroelectric Hf_{0.5}Zr_{0.5}O₂ films on SrTiO₃(110). Nanoscale, 2022, 14, 2337-2343.	5.6	19
3	Large enhancement of ferroelectric polarization in Hf_{0.5}Zr_{0.5}O₂ films by low plasma energy pulsed laser deposition. Journal of Materials Chemistry C, 2022, 10, 1084-1089.	5.5	10
4	Bendable Polycrystalline and Magnetic CoFe₂O₄ Membranes by Chemical Methods. ACS Applied Materials & Interfaces, 2022, 14, 12845-12854.	8.0	17
5	Impact of non-ferroelectric phases on switching dynamics in epitaxial ferroelectric Hf0.5Zr0.5O2 films. APL Materials, 2022, 10, .	5.1	7
6	Enhanced electroresistance endurance of capped Hf0.5Zr0.5O2 ultrathin epitaxial tunnel barriers. APL Materials, 2022, 10, .	5.1	7
7	Voltage-driven strain-mediated modulation of exchange bias in Ir₂₀Mn₈₀/Fe₈₀Ga₂₀/Ta/âŸ¨011âŸ©-oriented PMN-32PT heterostructures. Applied Physics Letters, 2022, 120, 142406.	3.3	2
8	Impact of In3+ cations on structure and electromagnetic state of Mâ˜type hexaferrites. Journal of Energy Chemistry, 2022, 69, 667-676.	12.9	95
9	Control of Layering in Aurivillius Phase Nanocomposite Thin Films and Influence on Ferromagnetism and Optical Absorption. ACS Applied Electronic Materials, 2022, 4, 1997-2004.	4.3	6
10	Ferroelectric Hf_{0.5}Zr_{0.5}O₂ films on SrTiO₃(111). Journal of Materials Chemistry C, 2022, 10, 8407-8413.	5.5	7
11	Bulk photovoltaic effect modulated by ferroelectric polarization back-switching. Applied Physics Letters, 2022, 120, 242901.	3.3	2
12	Quenching of an antiferromagnet into high resistivity states using electrical or ultrashort optical pulses. Nature Electronics, 2021, 4, 30-37.	26.0	31
13	Enhancement of phase stability and optoelectronic performance of BiFeO₃thin filmsviacation co-substitution. Journal of Materials Chemistry C, 2021, 9, 330-339.	5.5	11
14	Non-volatile optical switch of resistance in photoferroelectric tunnel junctions. Nature Communications, 2021, 12, 382.	12.8	32
15	Thickness effect on the ferroelectric properties of La-doped HfO₂ epitaxial films down to 4.5 nm. Journal of Materials Chemistry C, 2021, 9, 12224-12230.	5.5	19
16	Epitaxial Ferroelectric HfO₂ Films: Growth, Properties, and Devices. ACS Applied Electronic Materials, 2021, 3, 1530-1549.	4.3	58
17	Stabilization of the Ferroelectric Phase in Epitaxial Hf_{1â€“x}Zr_xO₂ Enabling Coexistence of Ferroelectric and Enhanced Piezoelectric Properties. ACS Applied Electronic Materials, 2021, 3, 2106-2113.	4.3	22
18	Structural features, magnetic and ferroelectric properties of SrFe10.8In1.2O19 compound. Materials Research Bulletin, 2021, 138, 111236.	5.2	52

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19	Switchable photovoltaic response in hexagonal LuMnO3 single crystals. Applied Physics Letters, 2021, 118, .	3.3	8
20	Giant Tuning of Electronic and Thermoelectric Properties by Epitaxial Strain in p-Type Sr-Doped LaCrO₃ Transparent Thin Films. ACS Applied Electronic Materials, 2021, 3, 3461-3471.	4.3	7
21	Insights into the atomic structure of the interface of ferroelectric <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Hf</mml:mi><mml:mrow><mml:mn>0.5</mml:mn> mathvariant="normal">O</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math> grown epitaxially on <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>La</mml:mi>. Physical Review Materials, 2021, 5, .	2.4	15
22	Polarization and Resistive Switching in Epitaxial 2 nm Hf_{0.5}Zr_{0.5}O₂ Tunnel Junctions. ACS Applied Electronic Materials, 2021, 3, 3657-3666.	4.3	33
23	Features of structure, magnetic state and electrodynamic performance of SrFe12â^'xInxO19. Scientific Reports, 2021, 11, 18342.	3.3	77
24	The origin of the dual ferroic properties in quasi-centrosymmetrical SrFe12â^'xInxO19 hexaferrites. Journal of Alloys and Compounds, 2021, 886, 161249.	5.5	37
25	Critical effect of the bottom electrode on the ferroelectricity of epitaxial Hf_{0.5}Zr_{0.5}O₂thin films. Journal of Materials Chemistry C, 2021, 9, 3486-3492.	5.5	21
26	Strain-Mediated Magnetoelectric Effects. , 2021, , .		1
27	High-Temperature Synthesis and Dielectric Properties of LaTaON₂. Inorganic Chemistry, 2021, 60, 16484-16491.	4.0	4
28	Impact of La Concentration on Ferroelectricity of La-Doped HfO₂ Epitaxial Thin Films. ACS Applied Electronic Materials, 2021, 3, 4809-4816.	4.3	22
29	Bulk photovoltaic effect in hexagonal LuMnO3 single crystals. Physical Review B, 2021, 104, .	3.2	7
30	Strain and voltage control of magnetic and electric properties of FeRh films. Journal Physics D: Applied Physics, 2020, 53, 023002.	2.8	15
31	Crystal and magnetic structures, magnetic and ferroelectric properties of strontium ferrite partially substituted with in ions. Journal of Alloys and Compounds, 2020, 821, 153412.	5.5	98
32	Unraveling Ferroelectric Polarization and Ionic Contributions to Electroresistance in Epitaxial Hf_{0.5}Zr_{0.5}O₂ Tunnel Junctions. Advanced Electronic Materials, 2020, 6, 1900852.	5.1	44
33	Magnetic and ferroelectric properties, crystal and magnetic structures of SrFe_{11.9}In_{0.1}O₁₉. Physica Scripta, 2020, 95, 044006.	2.5	5
34	Thermal evolution of ferroelectric behavior in epitaxial Hf0.5Zr0.5O2. Applied Physics Letters, 2020, 117, .	3.3	14
35	Engineering Polar Oxynitrides: Hexagonal Perovskite BaWON₂. Angewandte Chemie - International Edition, 2020, 59, 18395-18399.	13.8	8
36	Engineering Polar Oxynitrides: Hexagonal Perovskite BaWON 2. Angewandte Chemie, 2020, 132, 18553-18557.	2.0	1

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37	Fatigue and retention in the growth window of ferroelectric Hf0.5Zr0.5O2 thin films. Applied Physics Letters, 2020, 117, .	3.3	22
38	Epitaxial Ferroelectric La-Doped Hf_{0.5}Zr_{0.5}O₂ Thin Films. ACS Applied Electronic Materials, 2020, 2, 3221-3232.	4.3	48
39	Materials Horizons Emerging Investigator Series: Ignasi Fina, Institute of Materials Science of Barcelona, Spain. Materials Horizons, 2020, 7, 1935-1936.	12.2	0
40	Local manipulation of metamagnetism by strain nanopatterning. Materials Horizons, 2020, 7, 2056-2062.	12.2	11
41	Blocking of Conducting Channels Widens Window for Ferroelectric Resistive Switching in Interfaceâ€Engineered Hf 0.5 Zr 0.5 O 2 Tunnel Devices. Advanced Functional Materials, 2020, 30, 2002638.	14.9	40
42	Flexible Antiferromagnetic FeRh Tapes as Memory Elements. ACS Applied Materials & Interfaces, 2020, 12, 15389-15395.	8.0	13
43	High polarization, endurance and retention in sub-5 nm Hf_{0.5}Zr_{0.5}O₂ films. Nanoscale, 2020, 12, 11280-11287.	5.6	72
44	Domain-Matching Epitaxy of Ferroelectric Hf_{0.5}Zr_{0.5}O₂(111) on La_{2/3}Sr_{1/3}MnO₃(001). Crystal Growth and Design, 2020, 20, 3801-3806.	3.0	60
45	Discovery of highly polarizable semiconductors BaZrS3 and Ba3Zr2S7. Physical Review Materials, 2020, 4, .	2.4	15
46	Engineering Ferroelectric Hf_{0.5}Zr_{0.5}O₂ Thin Films by Epitaxial Stress. ACS Applied Electronic Materials, 2019, 1, 1449-1457.	4.3	105
47	Enhanced ferroelectricity in epitaxial Hf0.5Zr0.5O2 thin films integrated with Si(001) using SrTiO3 templates. Applied Physics Letters, 2019, 114, .	3.3	61
48	Disentangling Highly Asymmetric Magnetoelectric Effects in Engineered Multiferroic Heterostructures. Physical Review Applied, 2019, 12, .	3.8	3
49	Direct Reversible Magnetoelectric Coupling in a Ferroelectric/Ferromagnetic Structure Controlled by Series Resistance Engineering. ACS Applied Electronic Materials, 2019, 1, 1937-1944.	4.3	8
50	Synergetic Electronic and Ionic Contributions to Electroresistance in Ferroelectric Capacitors. Advanced Electronic Materials, 2019, 5, 1800646.	5.1	15
51	Epitaxial Integration on Si(001) of Ferroelectric Hf_{0.5}Zr_{0.5}O₂ Capacitors with High Retention and Endurance. ACS Applied Materials & Interfaces, 2019, 11, 6224-6229.	8.0	47
52	Towards Oxide Electronics: a Roadmap. Applied Surface Science, 2019, 482, 1-93.	6.1	236
53	Complementary Resistive Switching Using Metalâ€“Ferroelectricâ€“Metal Tunnel Junctions. Small, 2019, 15, e1805042.	10.0	12
54	Vehicle Classification System Based on Ferroelectric Materials. , 2019, , .		0

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55	Asymmetric Resistive Switching Dynamics in BaTiO₃ Tunnel Junctions. Advanced Electronic Materials, 2019, 5, 1800407.	5.1	11
56	Band Gap Tuning of Solution-Processed Ferroelectric Perovskite BiFe_{1â€“x}Co_xO₃ Thin Films. Chemistry of Materials, 2019, 31, 947-954.	6.7	69
57	Growth Window of Ferroelectric Epitaxial Hf_{0.5}Zr_{0.5}O₂ Thin Films. ACS Applied Electronic Materials, 2019, 1, 220-228.	4.3	75
58	Disclosing odd symmetry, strain driven magnetic response of Co on Pt/PMN-PT (0â€‰1â€‰1). Journal of Physics Condensed Matter, 2019, 31, 084003.	1.8	1
59	The multiple directions of antiferromagnetic spintronics. Nature Physics, 2018, 14, 200-203.	16.7	365
60	Tailoring Lattice Strain and Ferroelectric Polarization of Epitaxial BaTiO3 Thin Films on Si(001). Scientific Reports, 2018, 8, 495.	3.3	36
61	Band structure of CuMnAs probed by optical and photoemission spectroscopy. Physical Review B, 2018, 97, .	3.2	22
62	High-temperature Magnetodielectric <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>Bi</mml:mi><mml:mo stretchy="false">(</mml:mo><mml:msub><mml:mi>Fe</mml:mi><mml:mrow><mml:mn>0.5</mml:mn></mml:mrow></mml:msub><m mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:math> Thin Films with Checkerboard-Ordered Oxyge. Physical Review Applied, 2018, 10, .	3.8	12
63	Reversible and magnetically unassisted voltage-driven switching of magnetization in FeRh/PMN-PT. Applied Physics Letters, 2018, 113, .	3.3	37
64	Selectable texture in epitaxial ferroelectric BaTiO₃ films integrated with silicon. CrystEngComm, 2018, 20, 6225-6229.	2.6	4
65	Control of Polar Orientation and Lattice Strain in Epitaxial BaTiO₃ Films on Silicon. ACS Applied Materials & Interfaces, 2018, 10, 25529-25535.	8.0	23
66	Robust ferroelectricity in epitaxial Hf1/2Zr1/2O2 thin films. Applied Physics Letters, 2018, 113, .	3.3	77
67	Control of the Polarization of Ferroelectric Capacitors by the Concurrent Action of Light and Adsorbates. ACS Applied Materials & Interfaces, 2018, 10, 23968-23975.	8.0	10
68	The Profile of Researchers Moving Towards Scientific Entrepreneurship. , 2018, , 143-157.		0
69	Electric-Field-Adjustable Time-Dependent Magnetoelectric Response in Martensitic FeRh Alloy. ACS Applied Materials & Interfaces, 2017, 9, 15577-15582.	8.0	29
70	Antiferromagnetic CuMnAs multi-level memory cell with microelectronic compatibility. Nature Communications, 2017, 8, 15434.	12.8	149
71	Mn 3dbands and Yâ€“O hybridization of hexagonal and orthorhombic YMnO₃thin films. Journal of Physics Condensed Matter, 2017, 29, 295501.	1.8	2
72	Hidden Magnetic States Emergent Under Electric Field, In A Room Temperature Composite Magnetoelectric Multiferroic. Scientific Reports, 2017, 7, 15460.	3.3	25

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73	Investigation of magneto-structural phase transition in FeRh by reflectivity and transmittance measurements in visible and near-infrared spectral region. New Journal of Physics, 2016, 18, 083017.	2.9	18
74	Unravelling and controlling hidden imprint fields in ferroelectric capacitors. Scientific Reports, 2016, 6, 25028.	3.3	23
75	High ferroelectric polarization in c-oriented BaTiO3 epitaxial thin films on SrTiO3/Si(001). Applied Physics Letters, 2016, 109, .	3.3	24
76	Dielectric characterization of multiferroic magnetoelectric double-perovskite Y(Ni0.5Mn0.5)O3 thin films. Applied Physics Letters, 2016, 109, .	3.3	7
77	Antiferromagnetic spintronics. Nature Nanotechnology, 2016, 11, 231-241.	31.5	1,578
78	Defect-induced magnetic structure of CuMnSb. Physical Review B, 2016, 94, .	3.2	8
79	Electric control of antiferromagnets. IEEE Transactions on Magnetics, 2016, , 1-1.	2.1	5
80	Strainâ€Controlled Responsiveness of Slave Halfâ€Doped Manganite La_{0.5}Sr_{0.5}MnO₃ Layers Inserted in BaTiO₃ Ferroelectric Tunnel Junctions. Advanced Electronic Materials, 2016, 2, 1600368.	5.1	21
81	Untangling Electrostatic and Strain Effects on the Polarization of Ferroelectric Superlattices. Advanced Functional Materials, 2016, 26, 6446-6453.	14.9	23
82	Multiple-stable anisotropic magnetoresistance memory in antiferromagnetic MnTe. Nature Communications, 2016, 7, 11623.	12.8	169
83	Isothermal anisotropic magnetoresistance in antiferromagnetic metallic IrMn. Scientific Reports, 2016, 6, 35471.	3.3	20
84	Monolithic integration of room-temperature multifunctional BaTiO3-CoFe2O4 epitaxial heterostructures on Si(001). Scientific Reports, 2016, 6, 31870.	3.3	19
85	Four-state ferroelectric spin-valve. Scientific Reports, 2015, 5, 9749.	3.3	38
86	Origin of tunnel electroresistance effect in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>PbTi</mml:mi><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>-based multiferroic tunnel junctions. Physical Review B, 2015, 92, .	3.2	29
87	In-plane tunnelling field-effect transistor integrated on Silicon. Scientific Reports, 2015, 5, 14367.	3.3	7
88	Prospect for Antiferromagnetic Spintronics. IEEE Transactions on Magnetics, 2015, 51, 1-4.	2.1	43
89	Selecting Steady and Transient Photocurrent Response in BaTiO₃ Films. Advanced Electronic Materials, 2015, 1, 1500171.	5.1	30
90	Nanocrystalline Ferroelectric BiFeO₃ Thin Films by Low-Temperature Atomic Layer Deposition. Chemistry of Materials, 2015, 27, 6322-6328.	6.7	24

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91	Switching magnetic order at an Fe/BaTiO<inf>3</inf> interface on and off: Impact on hybrid magnetic-ferroelectric tunnel junctions. , 2015, , .		0
92	Electric control of magnetism at the Fe/BaTiO3 interface. Nature Communications, 2014, 5, 3404.	12.8	179
93	Multiferroic Iron Oxide Thin Films at Room Temperature. Advanced Materials, 2014, 26, 4645-4652.	21.0	172
94	Room-temperature antiferromagnetic memory resistor. Nature Materials, 2014, 13, 367-374.	27.5	546
95	Tailoring the interfacial magnetic anisotropy in multiferroic field-effect devices. Physical Review B, 2014, 90, .	3.2	24
96	Spintronic Functionality of BiFeO₃ Domain Walls. Advanced Materials, 2014, 26, 7078-7082.	21.0	56
97	Anisotropic magnetoresistance in an antiferromagnetic semiconductor. Nature Communications, 2014, 5, 4671.	12.8	136
98	The direct magnetoelectric effect in ferroelectricâ€“ferromagnetic epitaxial heterostructures. Nanoscale, 2013, 5, 8037.	5.6	49
99	Tetragonal phase of epitaxial room-temperature antiferromagnet CuMnAs. Nature Communications, 2013, 4, 2322.	12.8	123
100	Phase coexistence and magnetically tuneable polarization in cycloidal multiferroics. Physical Review B, 2013, 88, .	3.2	14
101	Ultra-flat BaTiO3 epitaxial films on Si(001) with large out-of-plane polarization. Applied Physics Letters, 2013, 102, .	3.3	53
102	Large out-of-plane ferroelectric polarization in flat epitaxial BaTiO3 on CoFe2O4 heterostructures. Applied Physics Letters, 2013, 102, .	3.3	26
103	Storing magnetic information in IrMn/MgO/Ta tunnel junctions via field-cooling. Applied Physics Letters, 2013, 102, .	3.3	56
104	Obtaining the structure factors for an epitaxial film using Cu X-ray radiation. Journal of Applied Crystallography, 2013, 46, 1749-1754.	4.5	16
105	Spin-phonon coupling in Gd(Co1/2Mn1/2)O3 perovskite. Journal of Applied Physics, 2013, 114, .	2.5	27
106	Epitaxy-distorted spin-orbit Mott insulator in Sr<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>IrO<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>4</mml:mn></mml:msub></mml:math>thin films. Physical Review B, 2013, 87, .	3.2	70
107	Electrical Measurement of Antiferromagnetic Moments in Exchange-Coupled<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>IrMn</mml:mi><mml:mo>/</mml:mo><mml:mi>NiFe</mml:mi></mml:math>Stacks. Physical Review Letters, 2013, 110, .	7.8	70
108	Strain-driven transition from <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>E</mml:mi></mml:math>-type to<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>A</mml:mi></mml:math>-type magnetic order in YMnO<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>3</mml:mn></mml:msub></mml:math>epitaxial films. Physical Review B, 2012, 86, .	3.2	22

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109	Scanning tunneling microscopy reveals LiMnAs is a room temperature anti-ferromagnetic semiconductor. Applied Physics Letters, 2012, 100, 112107.	3.3	11
110	Correlation between growth dynamics and dielectric properties of epitaxial BaTiO₃ films. Applied Physics Letters, 2012, 100, 102904.	3.3	19
111	Ferroelectric phase transition in strained multiferroic (Bi0.9La0.1)2NiMnO6 thin films. Applied Physics Letters, 2012, 100, .	3.3	12
112	Dielectric properties of (Bi<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML") Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 647	3.2	24
113	xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml: Dielectric response of epitaxially strained CoFe2O4spinel thin films. Physical Review B, 2012, 86, .	3.2	29
114	Surface phase transitions in BiFeO<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>3</mml:mn></mml:msub></mml:math>below room temperature. Physical Review B, 2012, 85, .	3.2	70
115	Room-temperature antiferromagnetism in CuMnAs. Journal of Magnetism and Magnetic Materials, 2012, 324, 1606-1612.	2.3	59
116	Ferroelectricity and strain effects in orthorhombic YMnO₃thin films. Phase Transitions, 2011, 84, 555-568.	1.3	16
117	Surface morphology and magnetic anisotropy in (Ga,Mn)As. Applied Physics Letters, 2011, 98, 152503.	3.3	10
118	A spin-valve-like magnetoresistance of an antiferromagnet-based tunnel junction. Nature Materials, 2011, 10, 347-351.	27.5	485
119	Diffusion of Mn interstitials in (Ga,Mn)As epitaxial layers. Physical Review B, 2011, 83, .	3.2	8
120	Magnetization Reversal by Electric-Field Decoupling of Magnetic and Ferroelectric Domain Walls in Multiferroic-Based Heterostructures. Physical Review Letters, 2011, 106, 057206.	7.8	121
121	X-ray interference effects on the determination of structural data in ultrathin La2/3Sr1/3MnO3 epitaxial thin films. Applied Physics Letters, 2011, 99, .	3.3	22
122	Demonstration of molecular beam epitaxy and a semiconducting band structure for I-Mn-V compounds. Physical Review B, 2011, 83, .	3.2	55
123	Chiral Domains in Cycloidal Multiferroic Thin Films: Switching and Memory Effects. Physical Review Letters, 2011, 107, 257601.	7.8	28
124	Nonferroelectric contributions to the hysteresis cycles in manganite thin films: A comparative study of measurement techniques. Journal of Applied Physics, 2011, 109, .	2.5	100
125	Magnetocapacitance in BaTiO3â€“CoFe2O4 nanocomposites. Thin Solid Films, 2010, 518, 4634-4636.	1.8	47
126	Structural and dielectric properties of (001) and (111)-oriented BaZr0.2Ti0.8O3 epitaxial thin films. Thin Solid Films, 2010, 518, 4692-4695.	1.8	10

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127	Dielectric anomalies in orthorhombic YMnO3 thin films. Thin Solid Films, 2010, 518, 4710-4713.	1.8	8
128	Emergence of ferromagnetism in antiferromagnetic TbMnO3 by epitaxial strain. Applied Physics Letters, 2010, 96, .	3.3	53
129	Density of Mn interstitials in (Ga,Mn)As epitaxial layers determined by anomalous x-ray diffraction. Applied Physics Letters, 2010, 97, .	3.3	6
130	Strain-driven noncollinear magnetic ordering in orthorhombic epitaxial YMnO3 thin films. Journal of Applied Physics, 2010, 108, .	2.5	25
131	Magnetic switch of polarization in epitaxial orthorhombic YMnO3 thin films. Applied Physics Letters, 2010, 97, .	3.3	42
132	Effects of morphology and strain on the dielectric response of multiferroic CoFe2O4â€“BaTiO3 nanocomposite thin films. Journal of Applied Physics, 2010, 108, 034108.	2.5	15
133	Strain tuned magnetoelectric coupling in orthorhombic YMnO3 thin films. Applied Physics Letters, 2009, 95, .	3.3	26
134	Enhanced thermal stability of Pt electrodes for flat epitaxial biferroic-YMnO3/Pt heterostructures. Applied Physics Letters, 2009, 95, 181907.	3.3	4
135	Epitaxial thin films of (Bi0.9La0.1)2NiMnO6 obtained by pulsed laser deposition. Journal of Magnetism and Magnetic Materials, 2009, 321, 1748-1753.	2.3	18
136	Dielectric properties of BaTiO3â€“CoFe2O4 nanocomposite thin films. Journal of Magnetism and Magnetic Materials, 2009, 321, 1795-1798.	2.3	14
137	Influence of substrate temperature in BiFeO3â€“CoFe2O4 nanocomposites deposited on SrTiO3 (001). Journal of Magnetism and Magnetic Materials, 2009, 321, 1790-1794.	2.3	14
138	Ferromagnetism in epitaxial orthorhombic YMnO3 thin films. Journal of Magnetism and Magnetic Materials, 2009, 321, 1719-1722.	2.3	38
139	Crystal texture selection in epitaxies of orthorhombic antiferromagnetic YMnO3 films. Thin Solid Films, 2008, 516, 4899-4907.	1.8	31
140	Dielectric anomaly and magnetic response of epitaxial orthorhombic YMnO₃ thin films. Journal of Materials Research, 2007, 22, 2096-2101.	2.6	25
141	Electric-Field Control of Exchange Bias in Multiferroic Epitaxial Heterostructures. Physical Review Letters, 2006, 97, 227201.	7.8	295
142	Exchange biasing and electric polarization with YMnO3. Applied Physics Letters, 2006, 89, 032510.	3.3	37
143	Optical Second-Harmonic Polarimetry on Hf_{0.5}Zr_{0.5}O₂/La_{0.67}Sr_{0.33}MnO₃ Interfaces. ACS Applied Electronic Materials, 0, , .	4.3	0